

EAST Search History**EAST Search History (Prior Art)**

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	5908	((216/19) or (216/67) or (216/75) or (216/79) or (216/80) or (438/695) or (438/710)). CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/12/13 21:53
L2	0	(conducting adj structures) and dielectric and substrate and (wiring adj layer) and (conductive adj protective adj layer) and (titanium adj nitride) and (cap adj layer) and mask and (photoresist adj layer) and (etch or etching) and gap and (deposit or depositing) and (high adj density adj plasma adj chemical adj vapor adj deposition) and (sputtering adj rate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2009/12/13 22:10

L3	0	(conducting adj structures) and dielectric and substrate and (wiring adj layer) and (conductive adj protective adj layer) and (titanium adj nitride) and (cap adj layer) and mask and photoresist and (etch or etching) and gap and (deposit or depositing) and (high adj density adj plasma adj chemical adj vapor adj deposition) and (sputtering adj rate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2009/12/13 22:12
L4	0	(conducting adj structures) and dielectric and substrate and (wiring adj layer) and (conductive adj protective adj layer) and (titanium adj nitride) and (cap adj layer) and photoresist and patterning and (etch or etching) and gap and (deposit or depositing) and (high adj density adj plasma adj chemical adj vapor adj deposition)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2009/12/13 22:14

EAST Search History (I nterference)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L5	0	(conducting adj structures) and dielectric and substrate and (wiring adj layer) and (conductive adj protective adj layer) and (titanium adj nitride) and (cap adj layer) and mask and (photoresist adj layer) and (etch or etching) and gap and (deposit or depositing) and (high adj density adj plasma adj chemical adj vapor adj deposition) and (sputtering adj rate)	USPAT; UPAD	OR	ON	2009/12/13 22:15
L6	0	(conducting adj structures) and dielectric and substrate and (wiring adj layer) and (conductive adj protective adj layer) and (titanium adj nitride) and (cap adj layer) and mask and photoresist and (etch or etching) and gap and (deposit or depositing) and (high adj density adj plasma adj chemical adj vapor adj deposition) and (sputtering adj	USPAT; UPAD	OR	ON	2009/12/13 22:15

		rate)				
L7	0	(conducting adj structures) and dielectric and substrate and (wiring adj layer) and (conductive adj protective adj layer) and (titanium adj nitride) and (cap adj layer) and photoresist and patterning and (etch or etching) and gap and (deposit or depositing) and (high adj density adj plasma adj chemical adj vapor adj deposition)	USPAT; UPAD	OR	ON	2009/12/13 22:15

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